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PTO/SB/08A (08-00)

Approved for use through 10/31/2002. OMB 0651-0031

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Substitute for form 1449A/PTO				<i>Complete if Known</i>	
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> <i>(use as many sheets as necessary)</i>				<u>Application Number</u>	
				<u>Filing Date</u>	February 1, 2001
				<u>First Named Inventor</u>	Koichiro TANAKA
				<u>Group Art Unit</u>	
				<u>Examiner Name</u>	
Sheet	1	of	1	Attorney Docket Number	740756-2256

## **U.S. PATENT DOCUMENTS**

## **FOREIGN PATENT DOCUMENTS**

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Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>

Examiner Signature		Date Considered	12/27/62
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Substitute for form 1449A/PTO		<i>Complete if Known</i>	
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> <i>(use as many sheets as necessary)</i>		Application Number	09/774,637
		Filing Date	February 1, 2001
		First Named Inventor	Koichiro TANAKA
		Group Art Unit	2815
		Examiner Name	J. Diaz
		Attorney Docket Number	0756-2256
Sheet	1	of	1

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D		U.S. Patent Application No. 09/741,026, including specification, drawings and filing receipt, "Laser Irradiation Apparatus and Method of Fabricating a Semiconductor Device" Koichiro TANAKA et al., December 21, 2000.	
			

Examiner Signature  Date Considered 12/26/02

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## INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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### Complete if Known

Application Number	09/774,637
Filing Date	February 1, 2001
First Named Inventor	Koichiro TANAKA
Group Art Unit	2815
Examiner Name	J. Diaz
Attorney Docket Number	0756-2256

### U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. <sup>1</sup>	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code <sup>2</sup> (if known)			
✓		4,330,363		Biegesen et al.	05/18/82	
✓		4,475,027		Pressley	10/02/84	
✓		4,733,944		Fahlen et al.	03/29/98	
✓		4,974,919		Muraki et al.	12/04/90	
✓		5,005,969		Kataoka	04/09/91	
✓		5,561,081		Takenouchi et al.	10/01/96	
✓		6,100,961		Shiraishi et al.	08/08/00	
✓		6,212,012		Tanaka	04/03/01	
✓		6,215,595		Yamazaki et al.	04/10/01	

### FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>6</sup>
		Office <sup>3</sup>	Number <sup>4</sup>	Kind Code <sup>5</sup> (if known)				

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✓		H. Endert et al., "Excimer Laser: A New Tool for Precision Micromachining," Optical and Quantum Electronics 27, 1995, pp. 1319-1335	
✓		H. Hayashi et al., "Fabrication of Low-Temperature Bottom-Gate Poly-Si TFTs on Large-Area Substrate by Linear-Beam Excimer Laser Crystallization and Ion Doping Method," IEDM95, 1995, pp. 829-832	
✓		Y. Helen et al., Reproducible High Field Effect Mobility Polysilicon Thin Film Transistors Involving Pulsed Nd:YVO <sub>4</sub> Laser Crystallization," IEDM99, 1999, pp. 297-300	

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